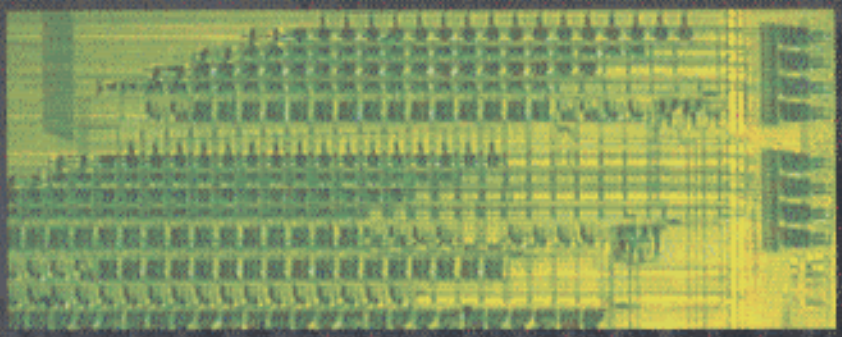

Low-Voltage, Low-Power Digital BiCMOS Circuits

Circuit Design, Comparative Study and Sensitivity Analysis

- BiCMOS design for today's fastest-growing applications
- Design concepts, in-depth analyses, and new methodologies
- Choosing the best BiCMOS circuit for your application
- Predicting and managing circuit performance sensitivities

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